

L Number	Hits	Search Text	DB	Time stamp
1	5719	electroless SAME copper	USPAT; US-PGPUB	2002/04/30 10:30
4	257	(electroless SAME copper) and damascene	USPAT; US-PGPUB	2002/04/30 10:37
22	128	((electroless SAME copper) and damascene)	USPAT; US-PGPUB	2002/04/30 10:37
-	2517	and (low WITH dielectric) damascene	USPAT; US-PGPUB	2002/04/30 10:29
-	1768	damascene and copper	USPAT; US-PGPUB	2002/04/25 15:37
-	1516	(damascene and copper) and dielectric	USPAT; US-PGPUB	2002/04/25 19:05
-	802	(damascene and copper) and (low WITH dielectric)	USPAT; US-PGPUB	2002/04/25 16:08
-	9	((damascene and copper) and (low WITH dielectric)) and "atomic layer deposition"	USPAT; US-PGPUB	2002/04/26 16:03
-	772	((damascene and copper) and (low WITH dielectric)) and (via or opening)	USPAT; US-PGPUB	2002/04/25 19:04
-	39	((damascene and copper) and (low WITH dielectric)) and (via or opening)) and (MSQ or MSZ or (methyl ADJ1 silsesquioxane))	USPAT; US-PGPUB	2002/04/25 16:22
-	1118	(damascene and copper) and (dielectric WITH (via or opening or recess or trench))	USPAT; US-PGPUB	2002/04/25 19:17
-	766	"dual damascene" and Copper and (dielectric WITH (via or opening or recess or trench))	USPAT; US-PGPUB	2002/04/25 19:20
-	410	("dual damascene" and Copper and (dielectric WITH (via or opening or recess or trench))) and ((etch or stop) ADJ2 layer)	USPAT; US-PGPUB	2002/04/25 19:20
-	180	"dual damascene" and Copper and ((low ADJ2 dielectric) WITH (via or opening or recess or trench))	USPAT; US-PGPUB	2002/04/25 19:20
-	120	("dual damascene" and Copper and ((low ADJ2 dielectric) WITH (via or opening or recess or trench))) and ((etch or stop) ADJ2 layer)	USPAT; US-PGPUB	2002/04/25 19:20
-	1912	(low WITH dielectric) SAME (via or groove)	USPAT; US-PGPUB	2002/04/26 15:13
-	11	((damascene and copper) and (low WITH dielectric)) and ("atomic layer deposition" or ALD)	USPAT; US-PGPUB	2002/04/26 16:04
-	7	((damascene and copper) and (low WITH dielectric)) and ("atomic layer deposition" or ALD) and tungsten	USPAT; US-PGPUB	2002/04/26 16:05
-	125	ALD and (tungsten wih nitride)	USPAT; US-PGPUB	2002/04/26 16:33
-	46	("atomic layer deposition" or ALD) and ("tungsten nitride" or WN)	USPAT; US-PGPUB	2002/04/29 17:17
-	17	("atomic layer deposition" or ALD) and (("tungsten nitride" or WN) WITH barrier)	USPAT; US-PGPUB	2002/04/29 17:18
-	8	("atomic layer deposition" or ALD) and (("tungsten nitride" or WN) WITH barrier) and (low WITH dielectric)	USPAT; US-PGPUB	2002/04/29 17:29
-	18	("atomic layer deposition" or ALD) and ("tungsten nitride" or WN) and (low WITH dielectric)	USPAT; US-PGPUB	2002/04/29 17:30
-	10	((("atomic layer deposition" or ALD) and ("tungsten nitride" or WN) and (low WITH dielectric)) NOT ((("atomic layer deposition" or ALD) and ((("tungsten nitride" or WN) WITH barrier) and (low WITH dielectric)))	USPAT; US-PGPUB	2002/04/29 17:38